FORM PTO-1449 TO BE FILED WITH INFORMATION DISCLOSURE STATEMENT

U.S. Department of Commerce	:	Atty. Docket No.: OSU1159-166B
Patent and Trademark Office	:	Serial No.: 10/649,046
	:	Filing Date: August 27, 2003
SUPPLEMENTAL INFORMATION	:	Applicant: Berger
DISCLOSURE STATEMENT	:	Group Art Unit: 2811
BY APPLICANTS	:	Examiner: Nadav

OTHER DOCUMENTS

SWC 1. Amlani, I. et al., Digital Logic Gate Using Quantum-Dot Cellular Automata, *Science*, 284, pp. 289-291 (April 9, 1999).

SWC 2. Fay, P. et al., Integration of InAs/A1Sb/GaSb Resonant Interband Tunneling Diodes with Heterostructure Field-Effect Transistors for Ultra-High-Speed Digital Circuit Applications, *IEEE*, pp. 162-165 (1999).

SWC 3. Fay, P. et al., A New Integrated Laboratory Course for Microwave Circuit Design and Measurements, *International Conference on Engineering and Computer Education*, Rio de Janeiro, 4 pages (August, 1999).

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U.S. PATENT DOCUMENTS

Examiner's Initial	Document Number	Date	Name	Class/Sub-class
	NONE			

FOREIGN PATENT DOCUMENTS

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	NONE			

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2. Amlani, I. et al., Demonstration of a six-dot quantum cellular automata system, *Applied Physics Letters*, 72, pp. 2179-2181 (1998).

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